

IR-Lumineszenzdiode (850 nm) mit hoher Ausgangsleistung
High Power Infrared Emitter (850 nm)
Lead (Pb) Free Product - RoHS Compliant
SFH 4550



Wesentliche Merkmale

- Infrarot LED mit hoher Ausgangsleistung
- Enger Abstrahlwinkel $\pm 3^\circ$
- Sehr hohe Strahlstärke
- Kurze Schaltzeiten

Anwendungen

- Infrarotbeleuchtung für CMOS Kameras
- Sensorik
- Datenübertragung

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

Features

- High Power Infrared LED
- Narrow emission angle $\pm 3^\circ$
- Very high radiant intensity
- Short switching times

Applications

- Infrared Illumination for CMOS cameras
- Sensor technology
- Data transmission

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Type Type	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$) Radiant Intensity Grouping ¹⁾ $I_e \text{ (mW/sr)}$
SFH 4550	Q65110A1772	≥ 400 (typ. 700)

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.001 \text{ sr}$ / measured at a solid angle of $\Omega = 0.001 \text{ sr}$

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}, T_{stg}	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Vorwärtsgleichstrom Forward current	I_F	100	mA
Stoßstrom, $t_p = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	1.5	A
Verlustleistung Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm ² Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 16 mm ² each	R_{thJA}	450	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$	λ_{peak}	860	nm
Centroid-Wellenlänge der Strahlung Centroid wavelength $I_F = 100\text{ mA}$	$\lambda_{centroid}$	850	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$	$\Delta\lambda$	42	nm
Abstrahlwinkel Half angle	φ	± 3	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm ²

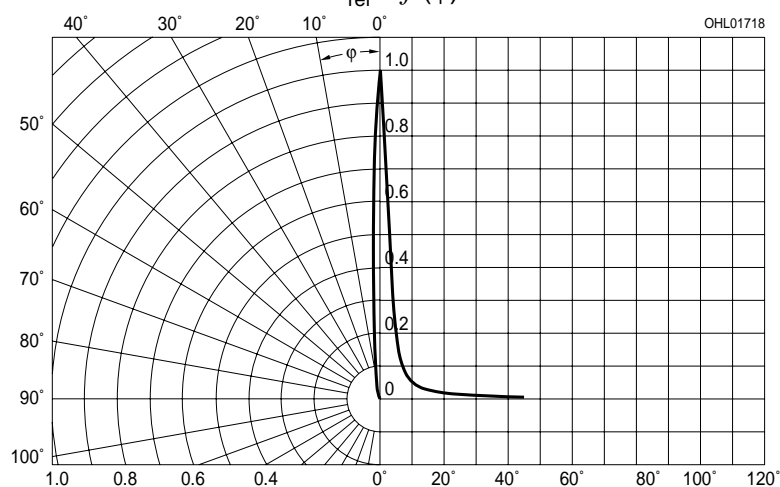
Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$	t_r, t_f	12	ns
Durchlassspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F V_F	1.5 (< 1.8) 2.4 (< 3.0)	V V
Sperrstrom Reverse current	I_R	not designed for reverse operation	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$\Phi_{e\text{ typ}}$	50	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 0.7	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.3	nm/K

Strahlstärke I_e in Achsrichtung¹⁾gemessen bei einem Raumwinkel $\Omega = 0.001$ sr**Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.001$ sr

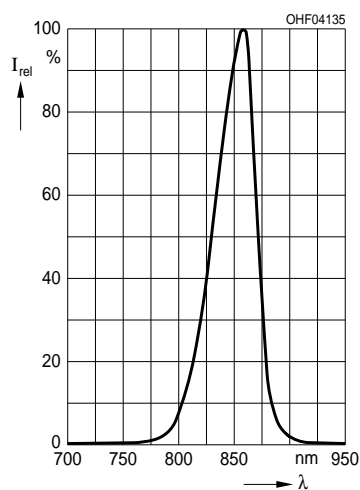
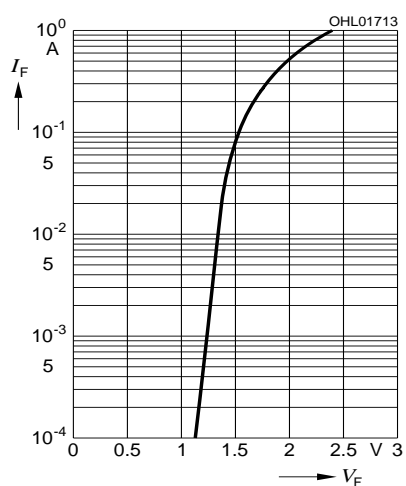
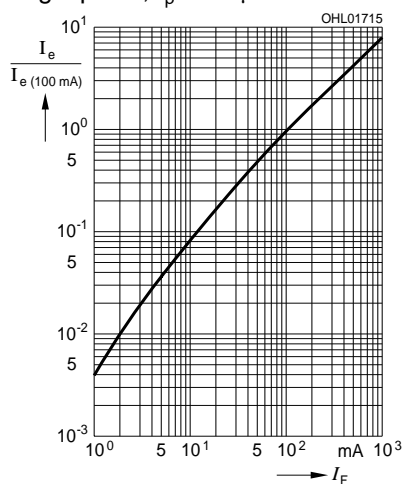
Bezeichnung Parameter	Symbol	Werte Values			Einheit Unit
		SFH 4550-DW	SFH 4550-EW	SFH 4550-FW	
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \min}$ $I_{e \max}$	400 800	630 1250	1000 2000	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ}}$	5000	7000	9000	mW/sr

¹⁾ Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1) /
Only one group in one packing unit (variation lower 2:1)

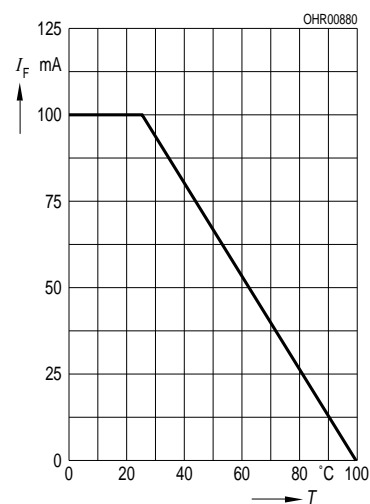
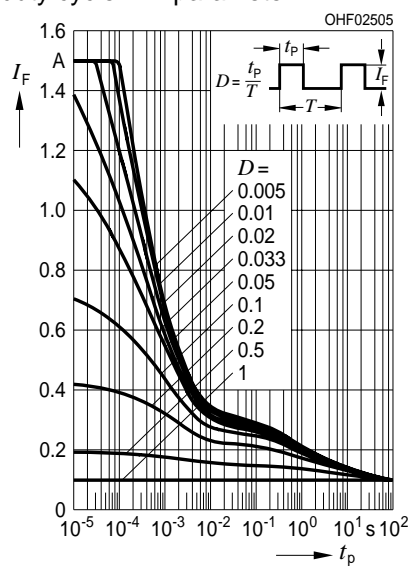
Abstrahlcharakteristik**Radiation Characteristics $I_{\text{rel}} = f(\varphi)$** 

Relative Spectral Emission

$$I_{\text{rel}} = f(\lambda)$$

**Forward Current $I_F = f(V_F)$** Single pulse, $t_p = 20 \mu\text{s}$ **Radiant Intensity $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$** Single pulse, $t_p = 20 \mu\text{s}$ **Max. Permissible Forward Current**

$$I_F = f(T_A), R_{\text{thJA}} = 450 \text{ K/W}$$

**Permissible Pulse Handling**Capability $I_F = f(\tau)$, $T_A = 25^\circ\text{C}$,
duty cycle $D = \text{parameter}$ 



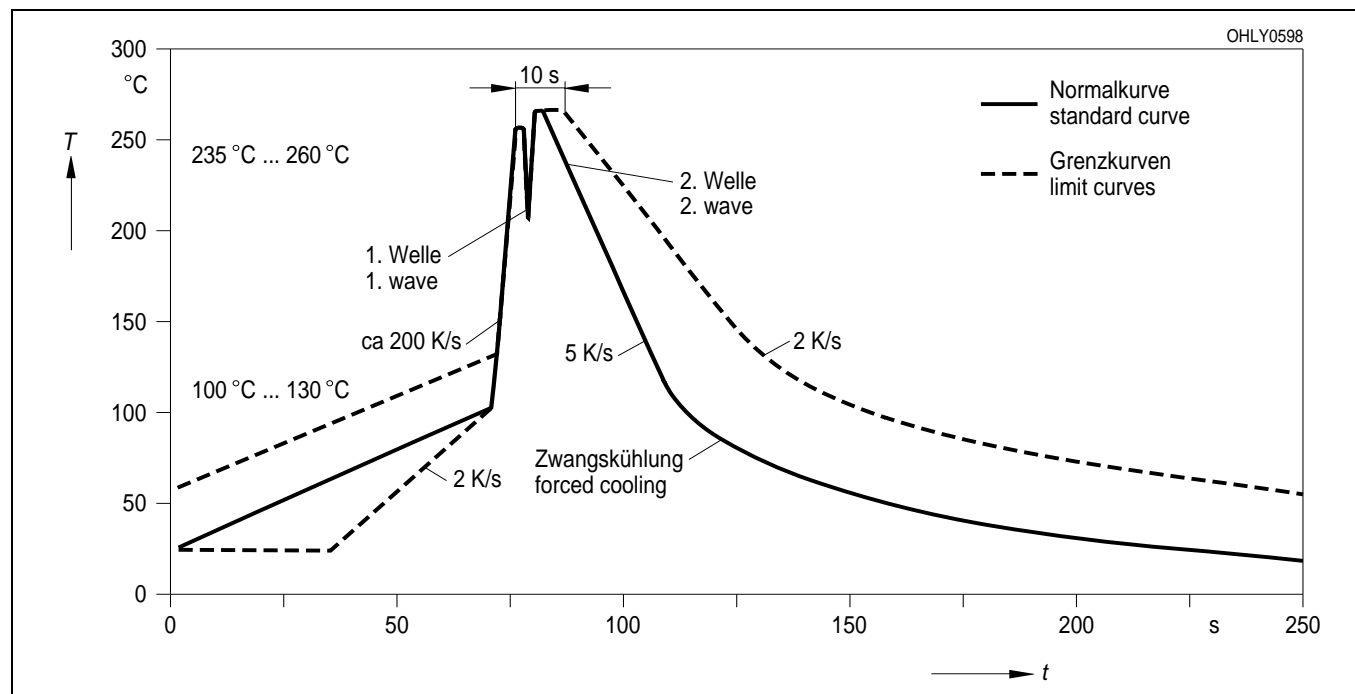
Wellenlöten TTW

TTW Soldering



Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
 (acc. to CECC 00802)



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¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.